Support Information

Grain Boundary Control of Organic Semiconductors via Solvent Vapor Annealing for High-Sensitivity NO_2 Detection

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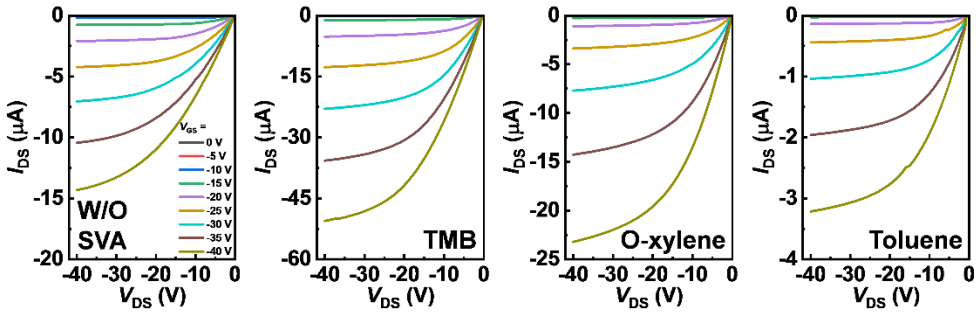


Figure S1. Output curves of the OTFTs with different SVA processes.

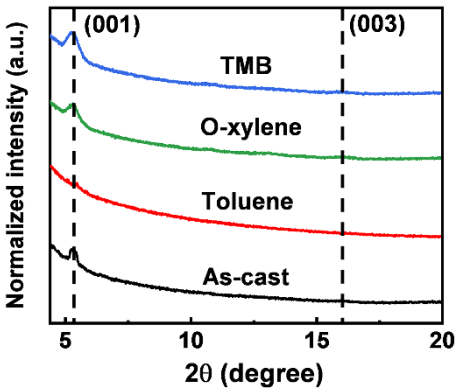


Figure S2. GIXRD patterns of TIPS-pentacene films with different processes.

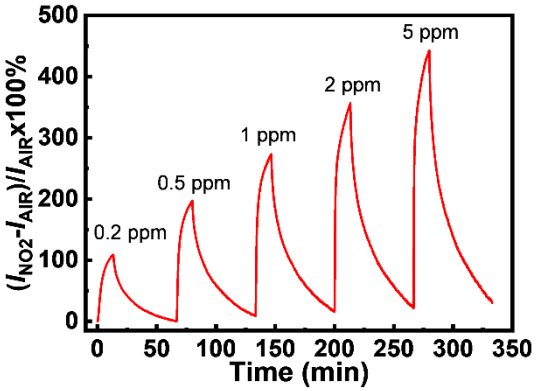


Figure S3. The recovery curve of the toluene treated device to dynamic NO_2 concentration at V_{DS} = V_{GS} = -40 V.

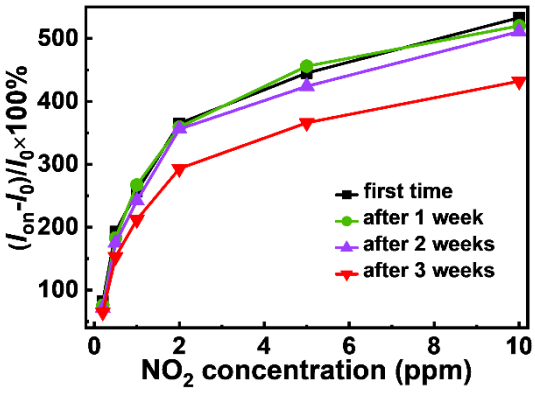


Figure S4. Responsivity of the devices after stored in atmosphere for 3 weeks to different NO2 concentrations.